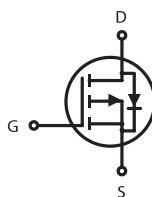
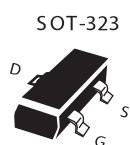


PRODUCT SUMMARY

V_{DS}	I_D	$R_{DS(ON)} (m\Omega)_{Max}$
-20V	-2A	145 @ $V_{GS} = -4.5V$ 195 @ $V_{GS} = -2.5V$

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- SOT-323 package.

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous ^a @ $T_C=25^\circ C$ -Pulsed ^b	I_D	-2	A
	I_{DM}	-7	A
Drain-Source Diode Forward Current ^a	I_S	-1	A
Maximum Power Dissipation ^a	P_D	1.0	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R_{thJA}	125	$^\circ C/W$
--	------------	-----	--------------